

Standard Rectifier Module



3~ Rectifier Bridge

Part number

VUO35-08NO7

Phase out

3~ Rectifier			
V _{RRM} =	800 V		
I _{DAV} =	35 A		
I _{FSM} =	400 A		



R E72873

20190201b



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-A

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- · Easy to mount with two screws
- Base plate: Aluminium
- internally DCB isolatedAdvanced power cycling

Recommended replacement: VUO35-12NO7

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

LIXYS

VUO35-08NO7

Phase out

Rectifier					Ratings	6	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{vJ} = 25^{\circ}C$			900	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{vJ} = 25^{\circ}C$			800	V
I _R	reverse current	$V_{\text{R}} = 800 \text{ V}$	$T_{vJ} = 25^{\circ}C$			40	μA
		V_{R} = 800 V	$T_{vJ} = 150^{\circ}C$			1.5	mA
VF	forward voltage drop	I _F = 15 A	$T_{vJ} = 25^{\circ}C$			1.10	V
		I _F = 45 A				1.38	V
		I _F = 15 A	T _{vJ} = 125 °C			1.01	۷
		I _F = 45 A				1.38	V
I dav	bridge output current	T _c = 85°C	T _{vJ} = 150°C			35	Α
		rectangular d = ⅓					
V _{F0}	threshold voltage		T _{vJ} = 150°C			0.80	V
r _F	slope resistance } for power	loss calculation only				12.9	mΩ
R _{thJC}	thermal resistance junction to ca	ise				4.2	K/W
R _{thCH}	thermal resistance case to heats	sink			0.6		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			29	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{vJ} = 45^{\circ}C$			400	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			430	Α
		t = 10 ms; (50 Hz), sine	T _{vJ} = 150°C			340	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			365	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{vJ} = 45^{\circ}C$			800	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			770	A ² s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150^{\circ}C$			580	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			555	A²s
C	junction capacitance	V _R = 400 V; f = 1 MHz	$T_{vJ} = 25^{\circ}C$		10		pF



20190201b



VUO35-08NO7

Phase out

Package	PWS-A				Ratings	5	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
	RMS current	per terminal				100	А
T _{vj}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					100		g
M _D	mounting torque			1.25		1.75	Nm
M _T	terminal torque			1.25		1.75	Nm
d _{Spp/App}	creepage distance on surface striking distance throug		terminal to terminal	6.5			mm
d _{Spb/Apb}	creepage ustance on surrace	sinking distance through an	terminal to backside	8.5			mm
V	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \le 1 \text{ mA}$	3000			V
		t = 1 minute		2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO35-08NO7	VUO35-08NO7	Box	20	502541

Equiv	alent Circuits for	Simulation	* on die level	T _{vj} = 150 °C
)- <u>R</u>	Rectifier		
V _{0 max}	threshold voltage	0.8		V
$\mathbf{R}_{0 \max}$	slope resistance *	11.7		mΩ



VUO35-08NO7







VUO35-08NO7

Phase out





Data according to IEC 60747 and per semiconductor unless otherwise specified